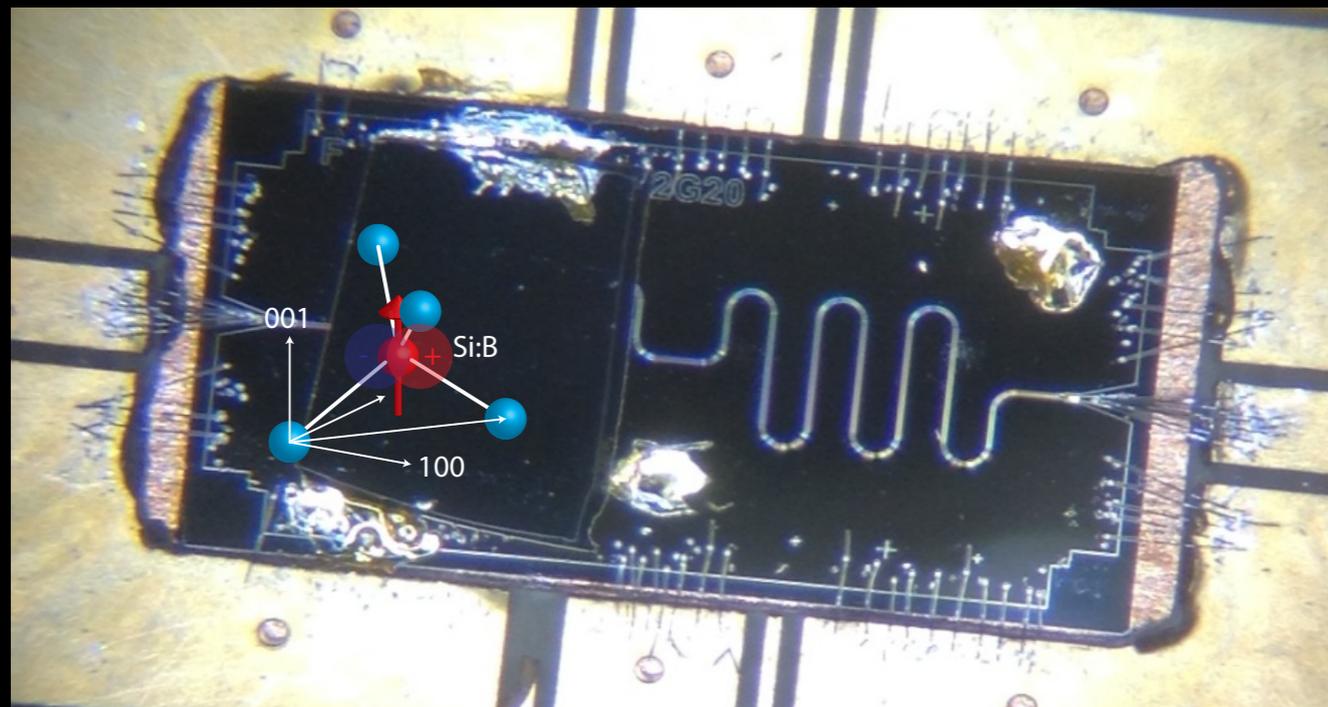


Engineering long coherence times of spin-orbit qubits in ^{28}Si



Asst. Prof. J. Salfi

Dept of Electrical and Computer Eng.
The University of British Columbia

RIKEN/Vancouver Joint Workshop

August 24, 2021

Kobayashi, **Salfi**, van der Heijden, Chua, Culcer, House, Johnson, McCallum, Riemann, Abrosimov, Becker, Pohl, Simmons, Rogge, *Nature Materials*, 20, 38-42 (2021)

Wang, Marcellina, Hamilton, Cullen, Rogge, **Salfi**, Culcer, *Nature Partner Journals: Quantum Information*, 7, 1-8 (2021)

Electron Spin Qubits in Silicon

What is special about ^{28}Si ?

Solid-state host with very long coherence times
 “Atoms in a semiconductor vacuum”

Donor ensembles

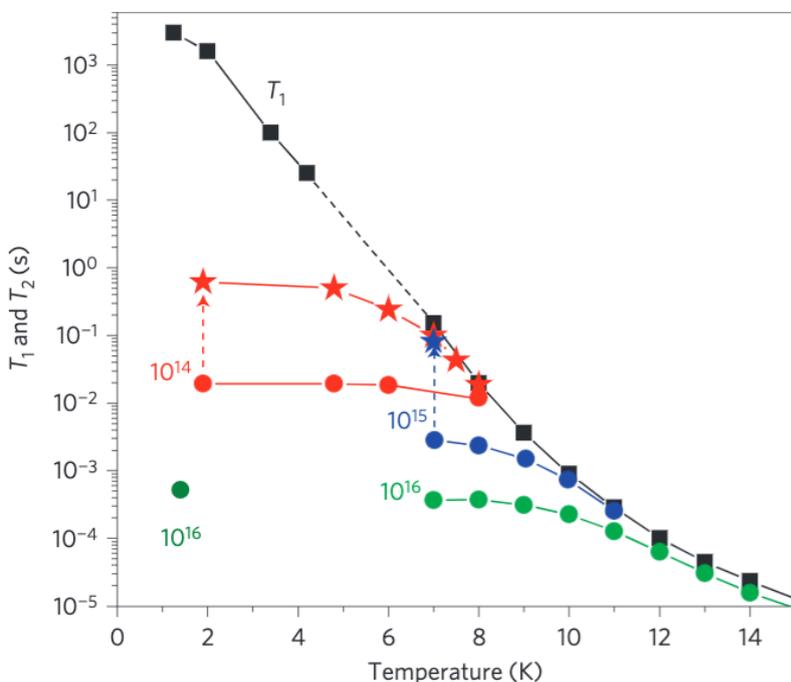
$T_2 \sim 10 \text{ ms to } 100 \text{ ms}$

Single donor

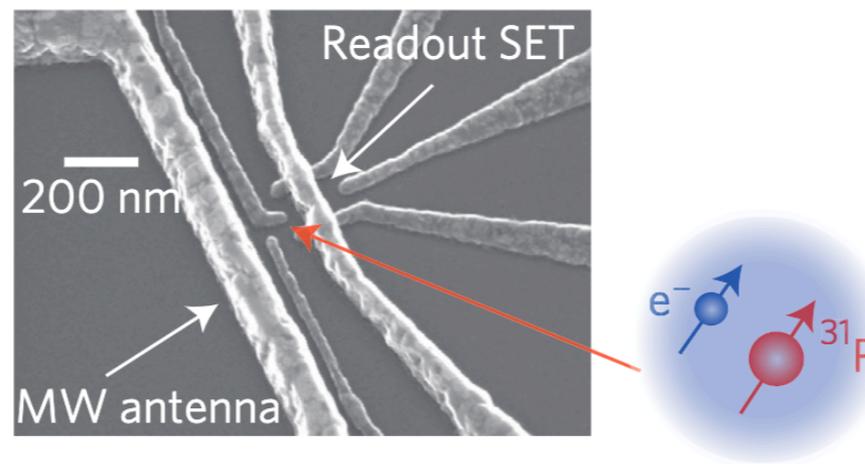
$T_2 \sim 100 \text{ ms}$

Single quantum dot

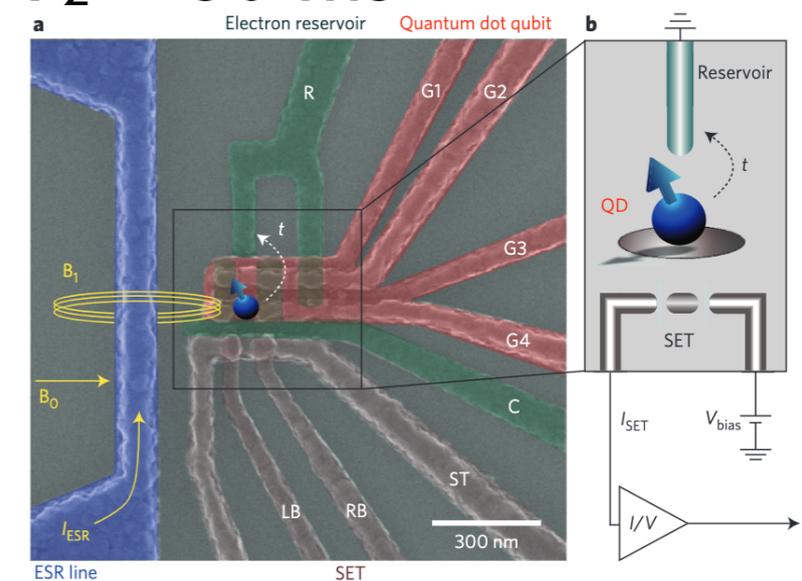
$T_2 \sim 30 \text{ ms}$



Tyryshkin et al,
 Nature Mat, 2011



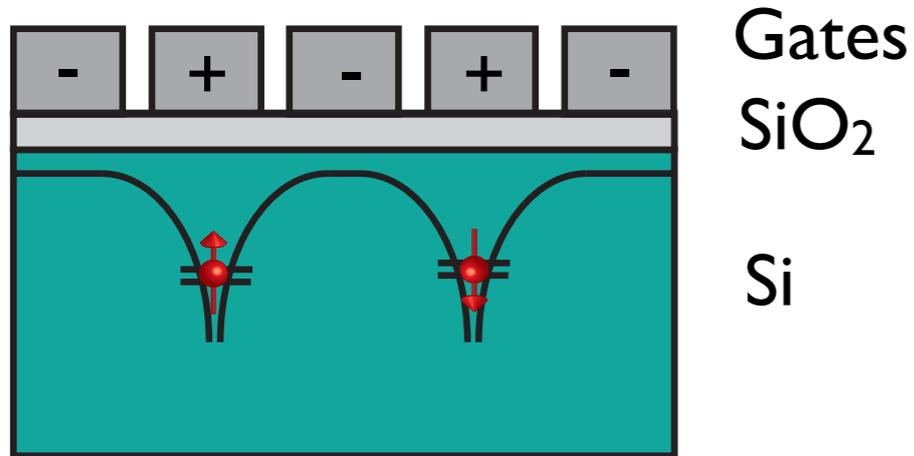
Muhonen et al,
 Nature Nano, 2014



Veldhorst et al,
 Nature Nano, 2014

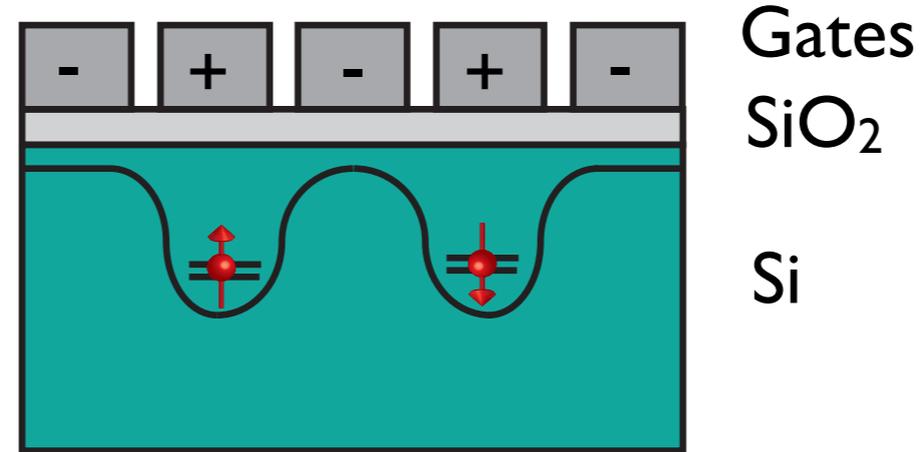
Electron Spin Qubits in Silicon

Donors $T_2 \sim 100$ ms



Muhonen et al Nature 2014

Quantum dots $T_2 \sim 30$ ms



Veldhorst et al Nature Nano 2014

Donor qubit measurement (spin to charge conversion) $e = 2 \times 10^{-3}$

Watson et al, Science Advances, 2016

Donor single qubit gates (magnetic resonance)

Dehollain et al NJP 2016

$e = 5 \times 10^{-4}$

Two-qubit gates (exchange interaction)

Huang et al Nature 2019

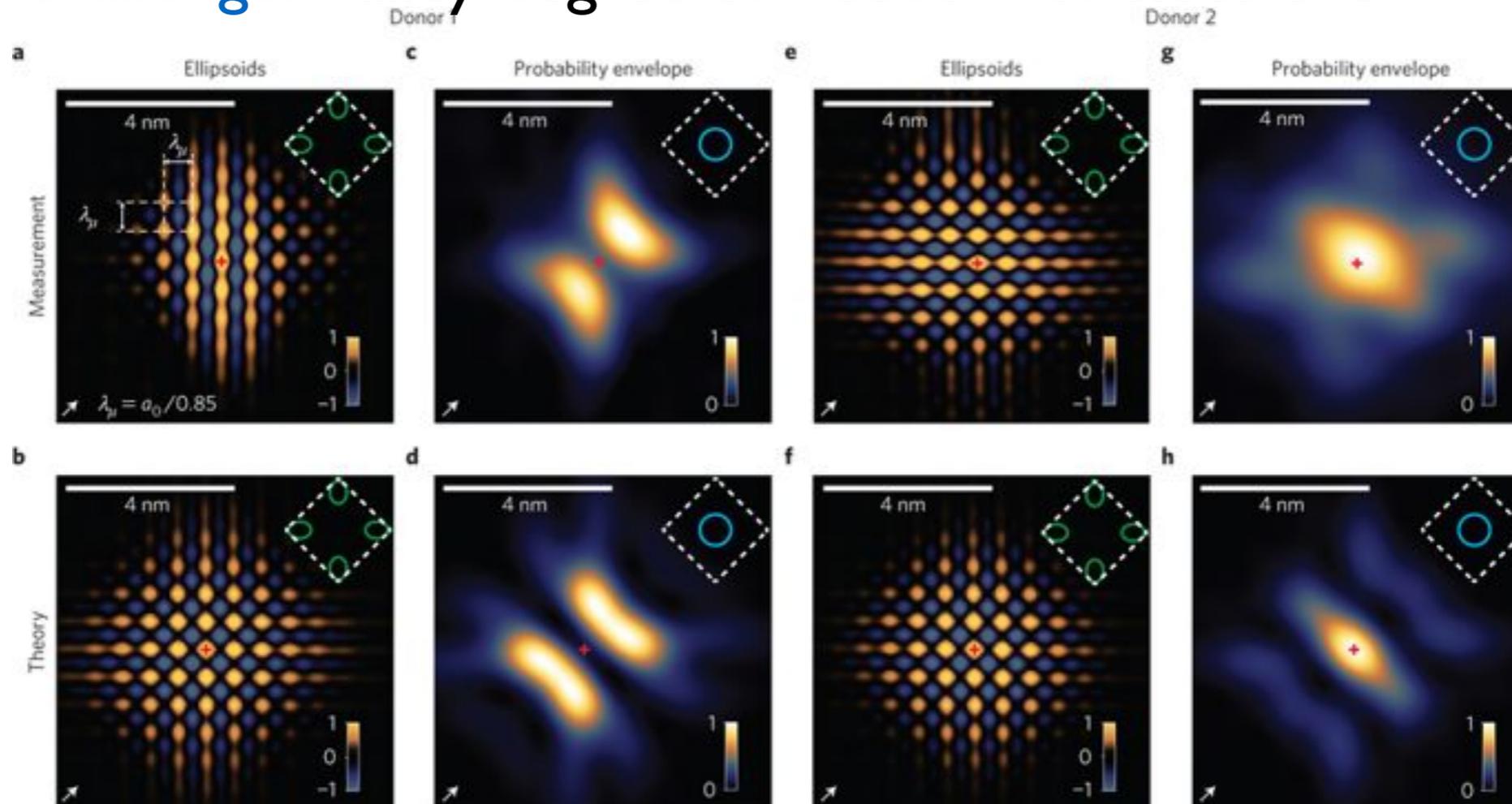
$e = 2 \times 10^{-2}$

Electron Spin Qubits in Silicon

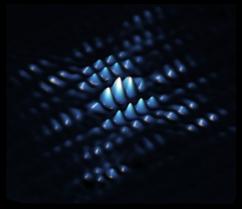
Summary: Small, clean qubits, manufacturable

Challenges with short-range interactions: electric noise (isotropic), cross-talk, density, range: ~ 20 nm (donor), ~ 100 nm (electron QD)

Additional challenge: Valley degree of freedom of electrons



Salfi et al Nature Materials 2014



Desiderata

Desiderata

Maintain long coherence time of spin qubits in ^{28}Si

Build long-range noise-insensitive multi-qubit gates

1. Capacitive interactions

2. Quantum electrodynamics (Q.E.D.) with microwave photons
[or acoustic phonons]

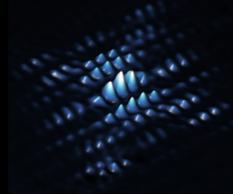
How to accomplish this?

***Enable electric control [or elastic control] for spin
Without spoiling coherence***

Why is this hard?

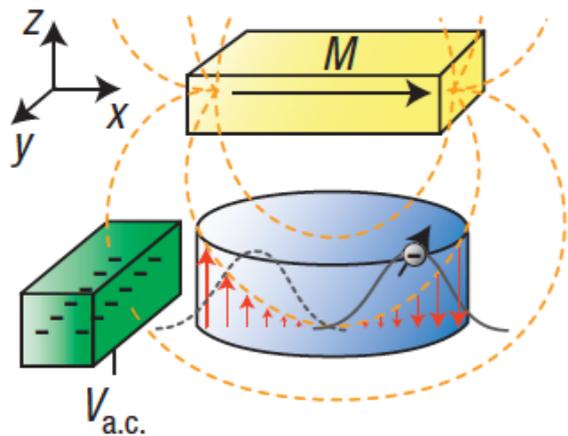
Si electron spin has weak intrinsic coupling to electric fields

Electric coupling is normally associated with fast decoherence



Electric Control

Artificial electric dipole: $E(t)$ moves electron $x(t)$, $B(x(t))$ from magnet



First demonstrated in GaAs [1]

Later shown for electrons in Si [2-5]

[1] Pioro-Ladrière et al NPhys. 2008

[3] Mi et al Nature 2018

[5] Yoneda et al, NNano 2018

[2] Kawakami et al NNano. 2014

[4] Samkharadze et al Science 2018

Intrinsic electric dipole: Electric field $E(t)$ moves electron, and it experiences time-varying $B(t)$ [special relativity] Thomas, Nature 1926

Strong spin decoherence [6-10] $T_2 \sim 0.1$ to $1 \mu\text{s}$

For electrons in Si, the effect is far too weak

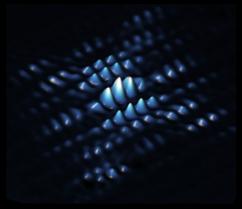
[6] Nowack et al Science 2007

[8] Maurand NComm 2016

[10] Hendrickx, arxiv:1904.11443

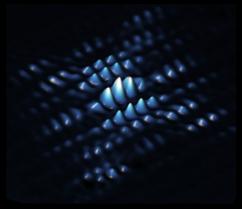
[7] Nadj-Perge et al Nature 2010

[9] Watsinger NComm 2018



Existential Question

Question: Is 1 μ s coherence time the best we can do with intrinsic spin orbit?

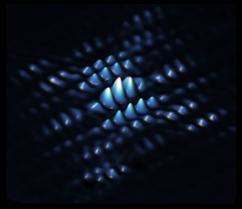


Existential Question

Question: Is 1 μ s coherence time the best we can do with intrinsic spin orbit?

Better question: How do we
[1] keep spin qubit coherence
[2] with strong intrinsic spin-orbit coupling

This would make hole spin a simple candidate for scalable quantum computation.



Existential Question

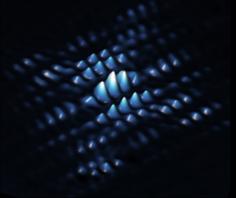
Question: Is 1 μ s coherence time the best we can do with intrinsic spin orbit?

Better question: How do we
[1] keep spin qubit coherence
[2] with strong intrinsic spin-orbit coupling

This would make hole spin a simple candidate for scalable quantum computation. **The conventional wisdom: this is not possible with intrinsic spin-orbit coupling**

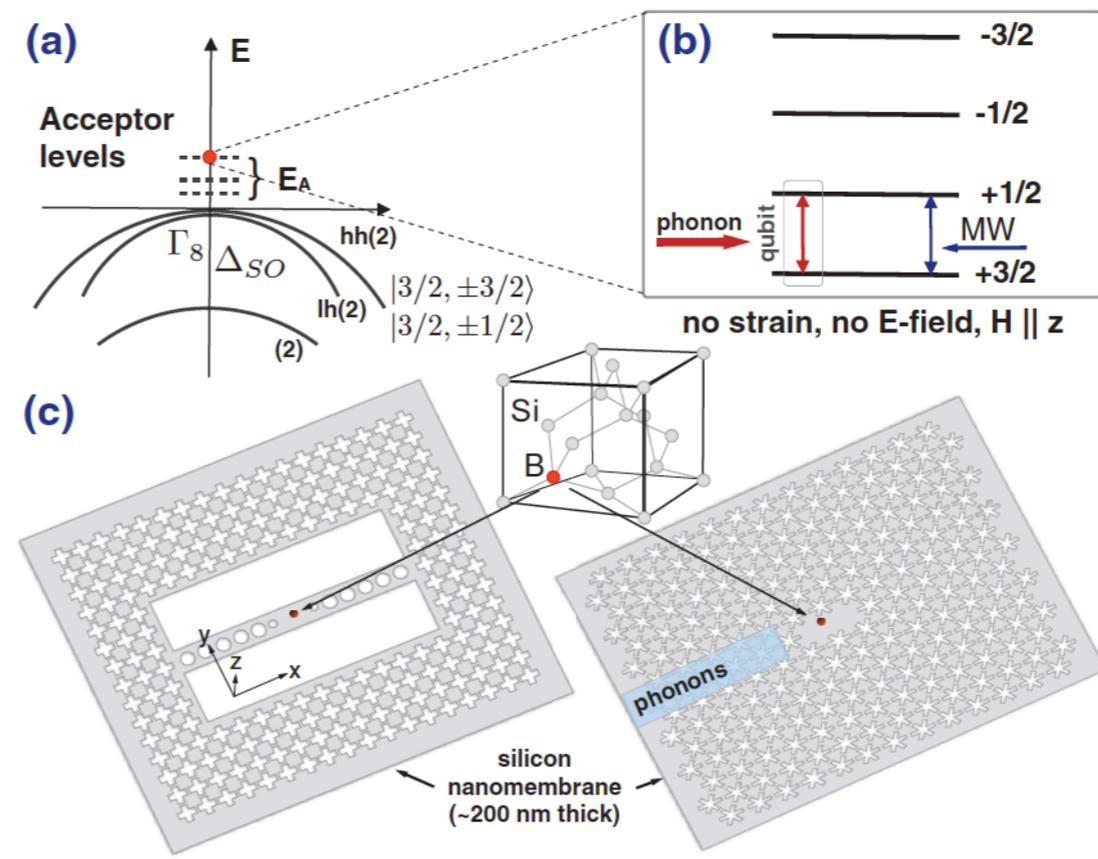
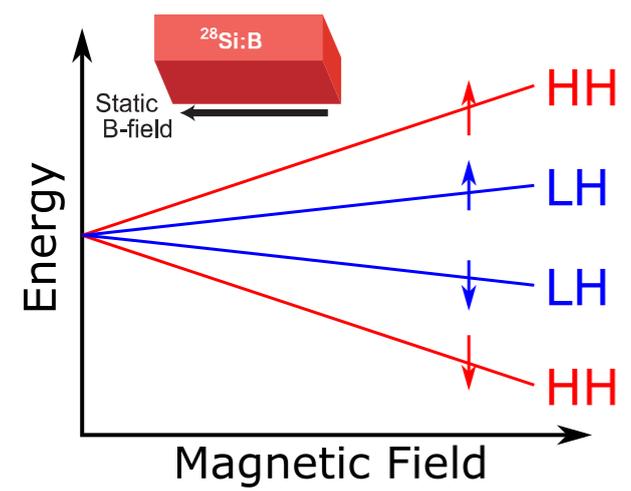
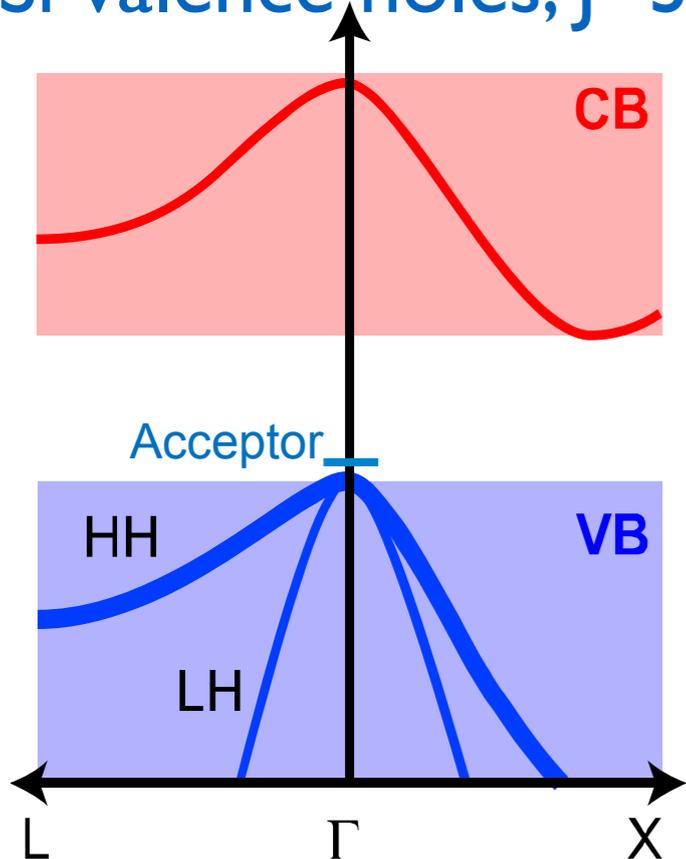
I will show you experiments demonstrating very long coherence times in a strong spin-orbit coupled system (spin is not a good quantum number).

Our model system: hole spin bound to Si:B



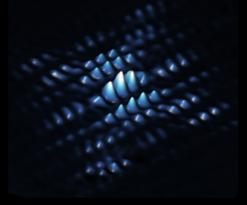
Si:B hole spin

Si valence holes, $J=3/2$ ~~and~~ L.S \rightarrow Quantized total angular momentum



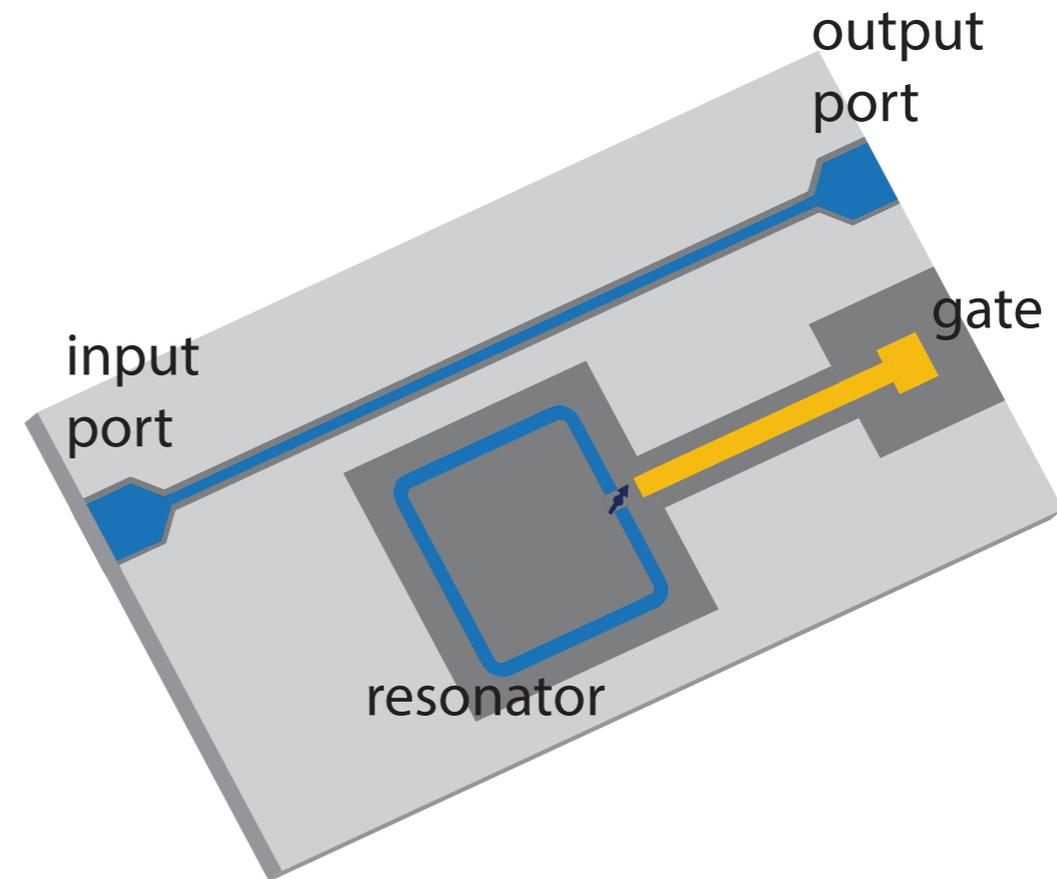
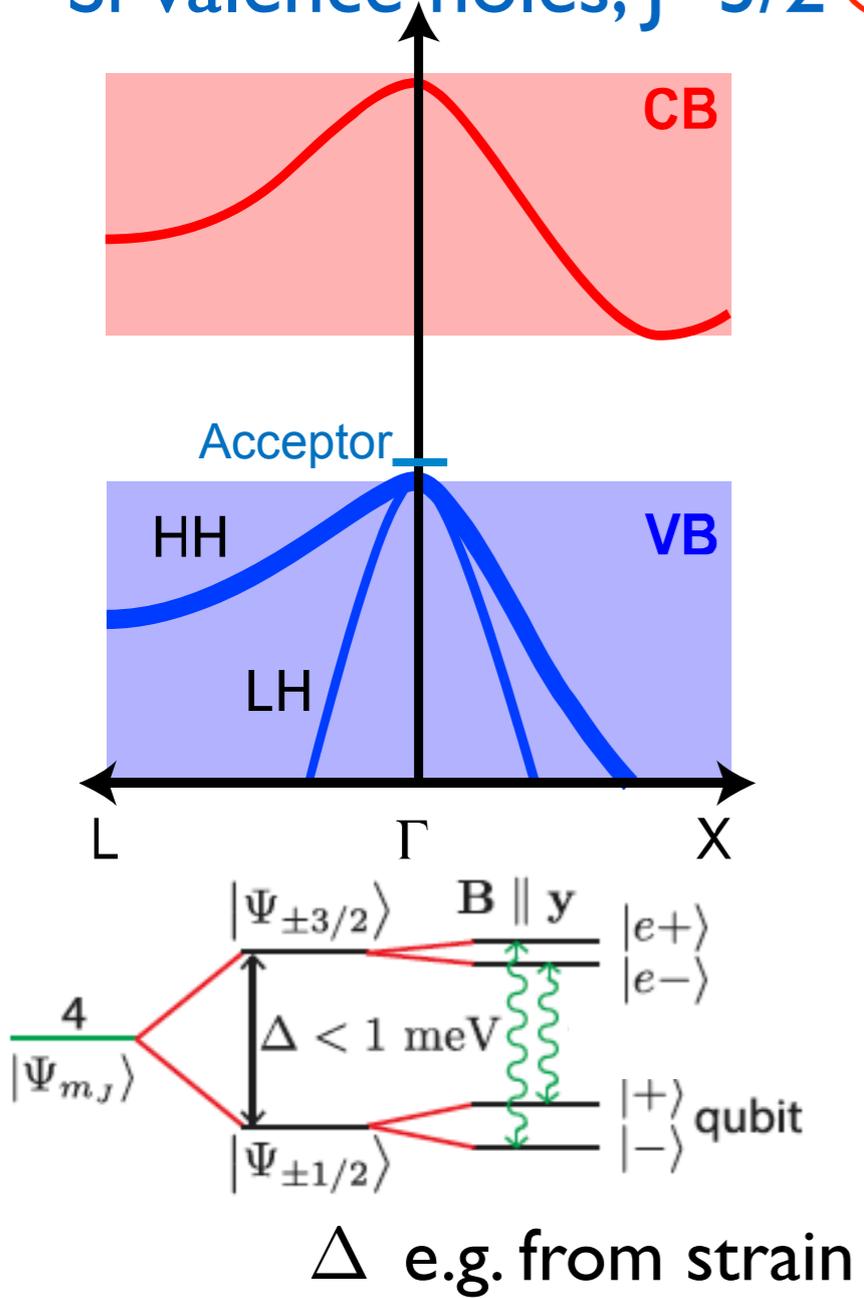
Long-ranged interactions
 Mediated by phonons
 Long relaxation times

Ruskov and Tahan PRB 2013



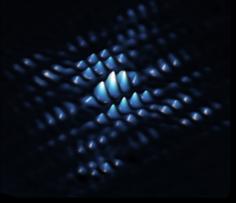
Si:B hole spin

Si valence holes, $J=3/2$ ~~↑ and ↓~~ L.S → Quantized total angular momentum



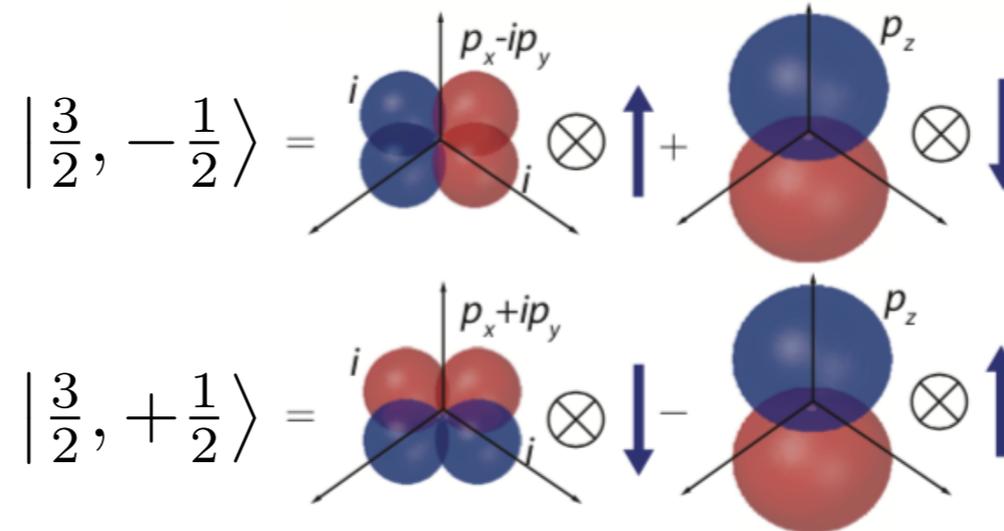
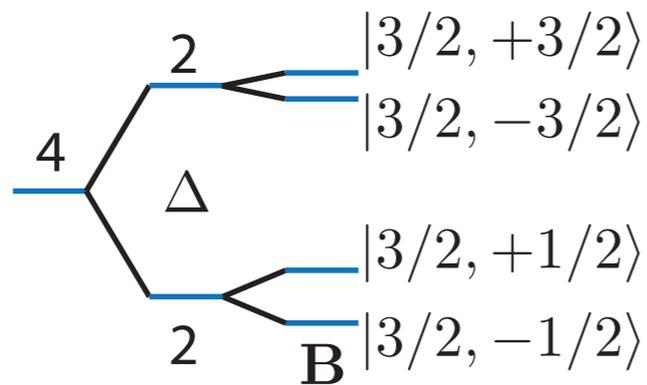
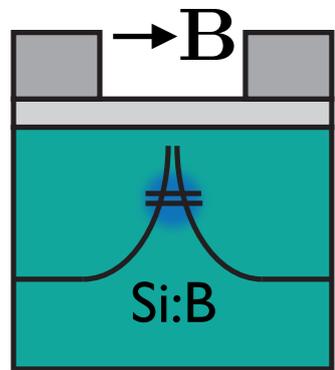
Long-ranged interactions
 Mediated electrically (or by photons)
 Long coherence times

Salfi, Mol, Culcer, Rogge PRL 2016
 Rogge, Salfi, Mol, US Patent 9,691,033



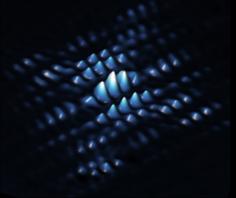
Si:B hole spin

Si valence holes, $J=3/2$ ~~↑ and ↓~~ L.S → Quantized total angular momentum



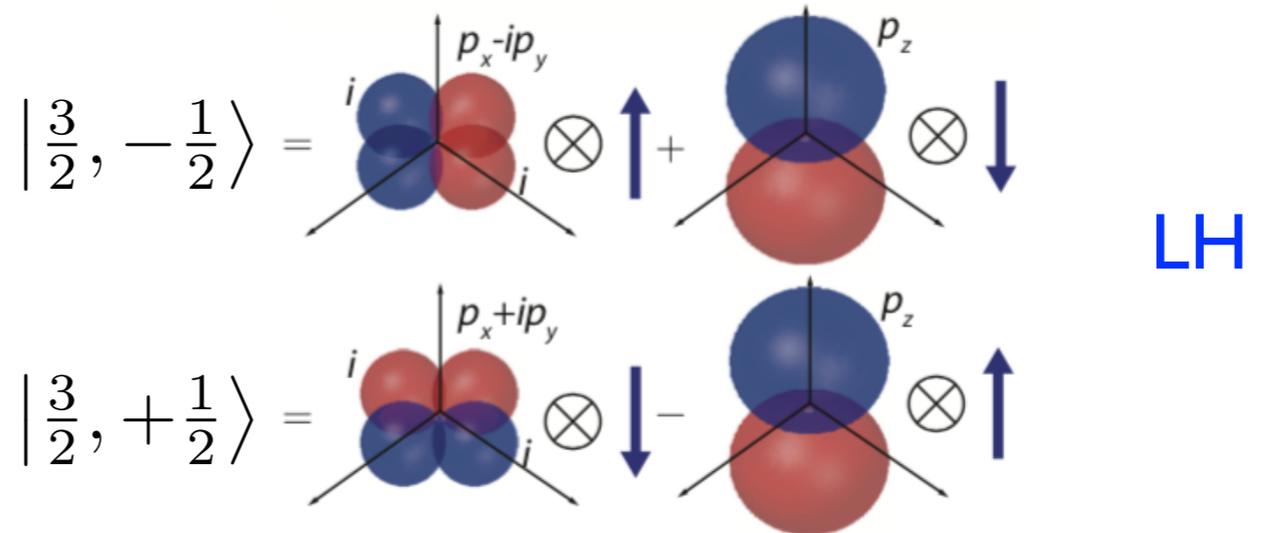
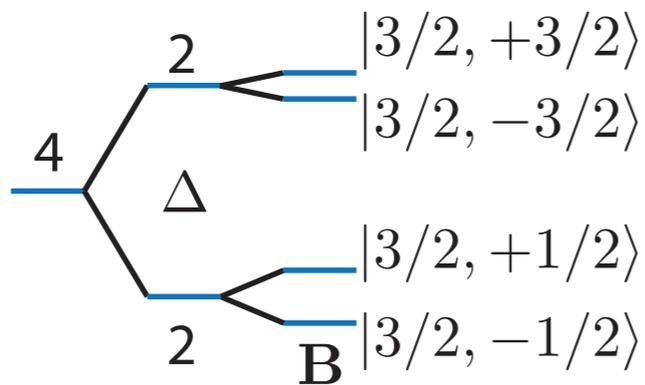
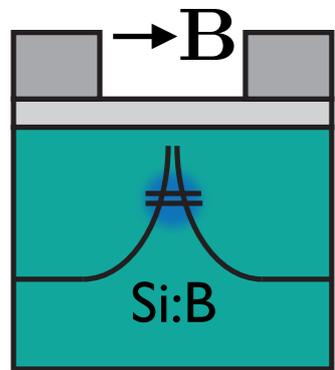
LH

Electric & elastic quadrupole + Zeeman ——— Electric & elastic dipole



Si:B hole spin

Si valence holes, $J=3/2$ ~~↑ and ↓~~ L.S → Quantized total angular momentum



Electric & elastic quadrupole + Zeeman — Electric & elastic dipole

Theory findings

I-qubit, 2-qubit gates:

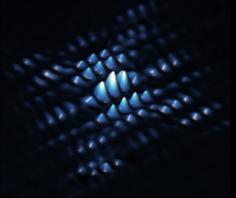
Strong electric dipole coupling

Coherence:

Robust to E field noise

Salfi et al PRL 2016





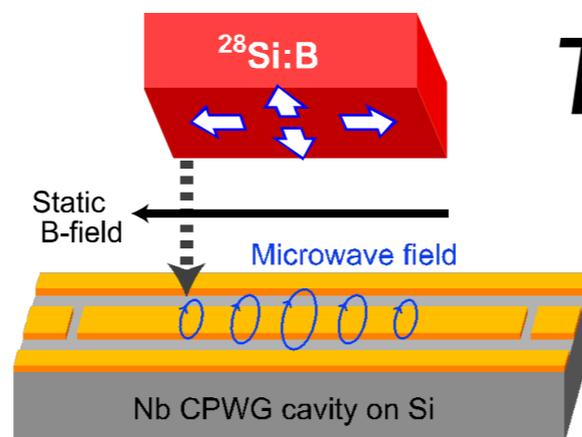
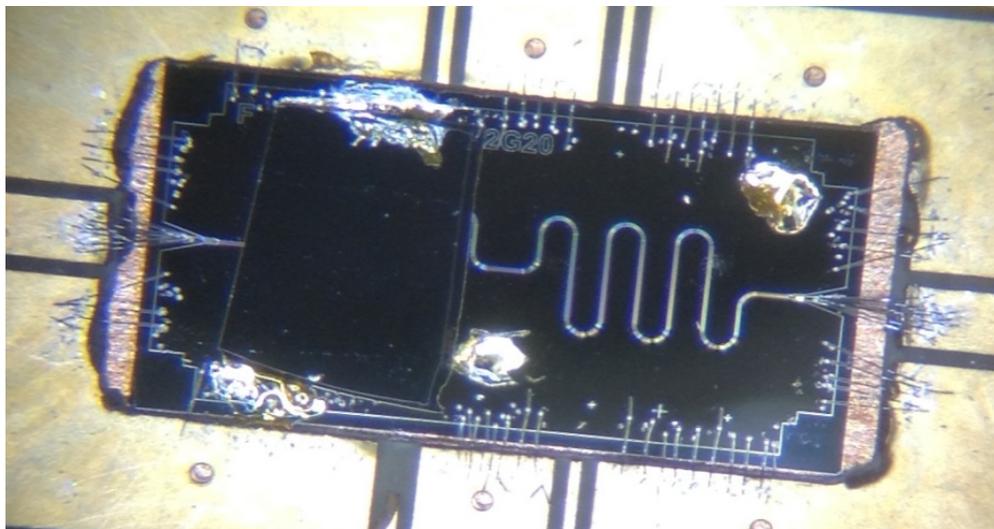
Hole spin coherence

Objective: Investigate and engineer hole spin coherence in Si:B atoms ^{28}Si , modest strain to engineer coherence and relaxation

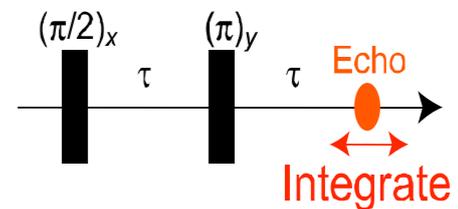
Methodology: Planar superconducting resonator

Technology to couple/measure/control superconducting qubits

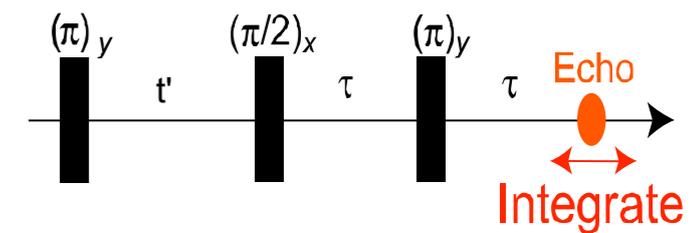
We use Nb rather than Aluminum (tolerates **B** field)



T_2 Hahn

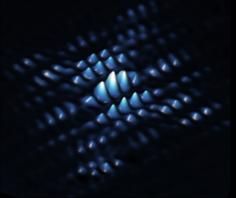


T_1



T_2 CPMG

Kobayashi, **Salfi** et al, Nature Materials, 20, 38-42 (2021)



Hole spin coherence

Prepare superposition

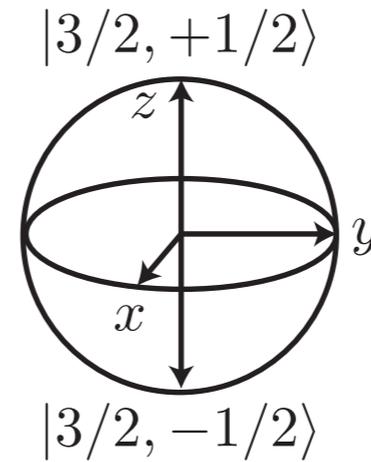
Apply $X(\pi/2)$ pulse (input)

Invert to enable refocusing

After time t , apply $X(\pi)$ pulse

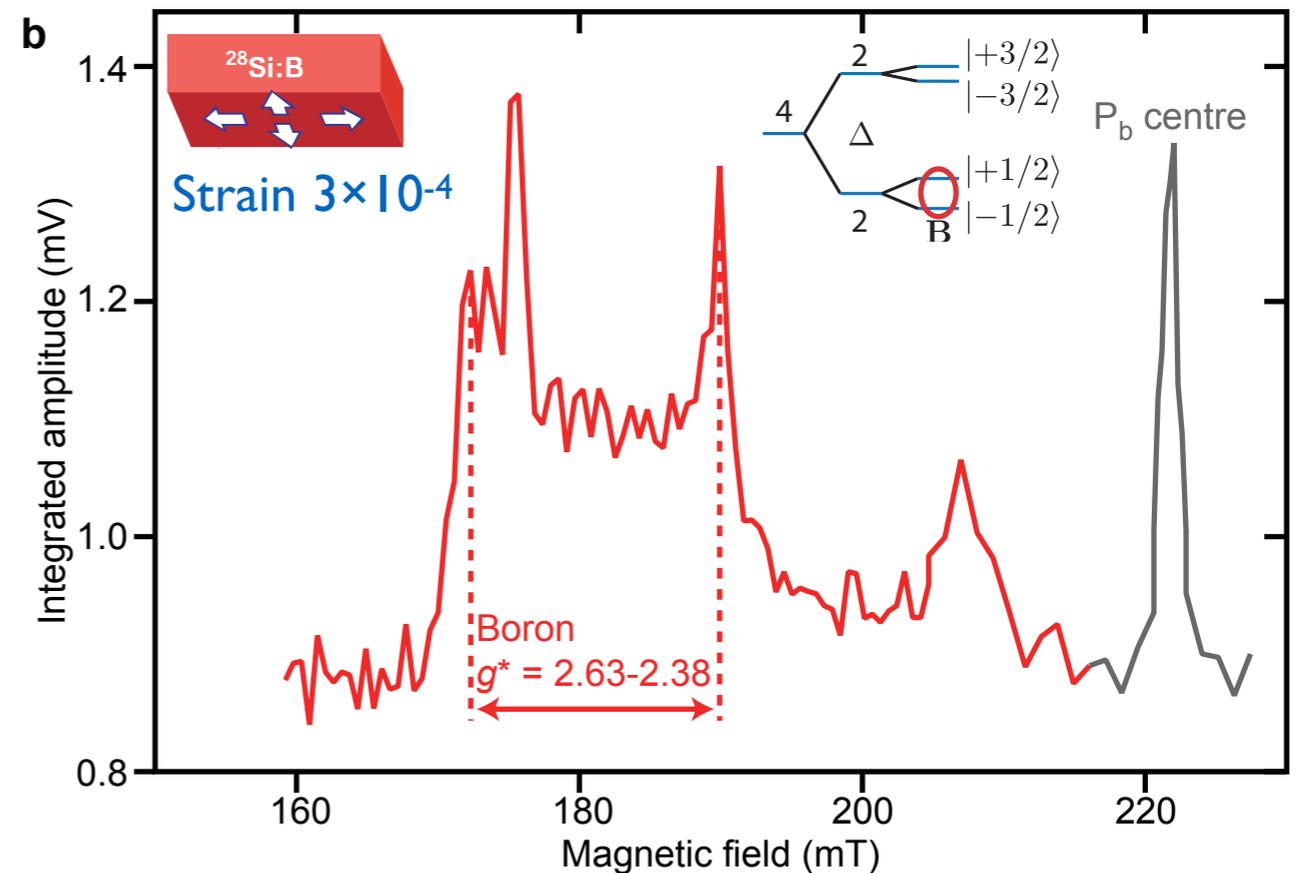
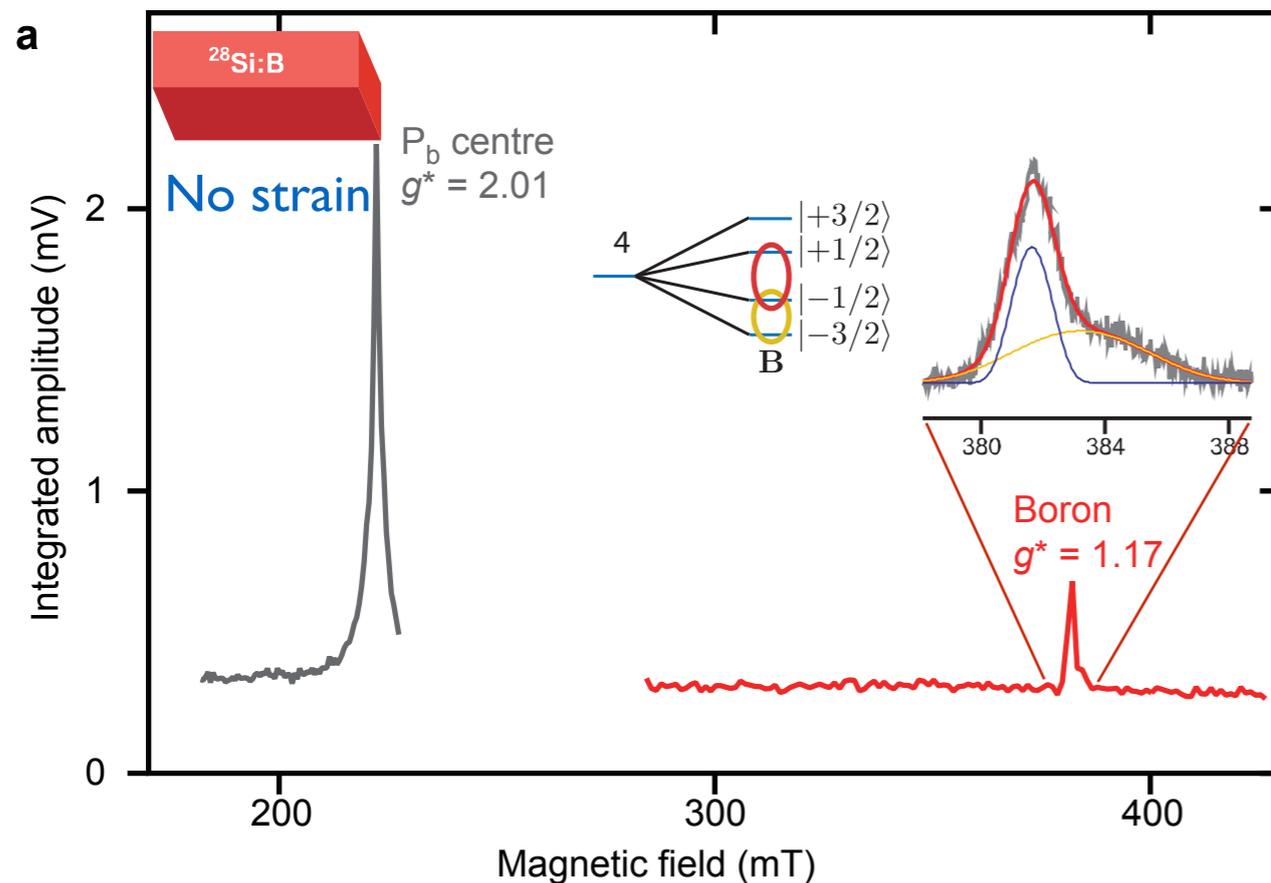
Hahn-echo

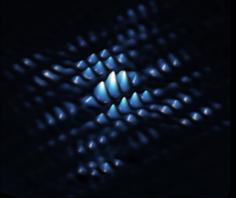
After time $2t$, refocusing (Hahn echo) is emitted into the resonator



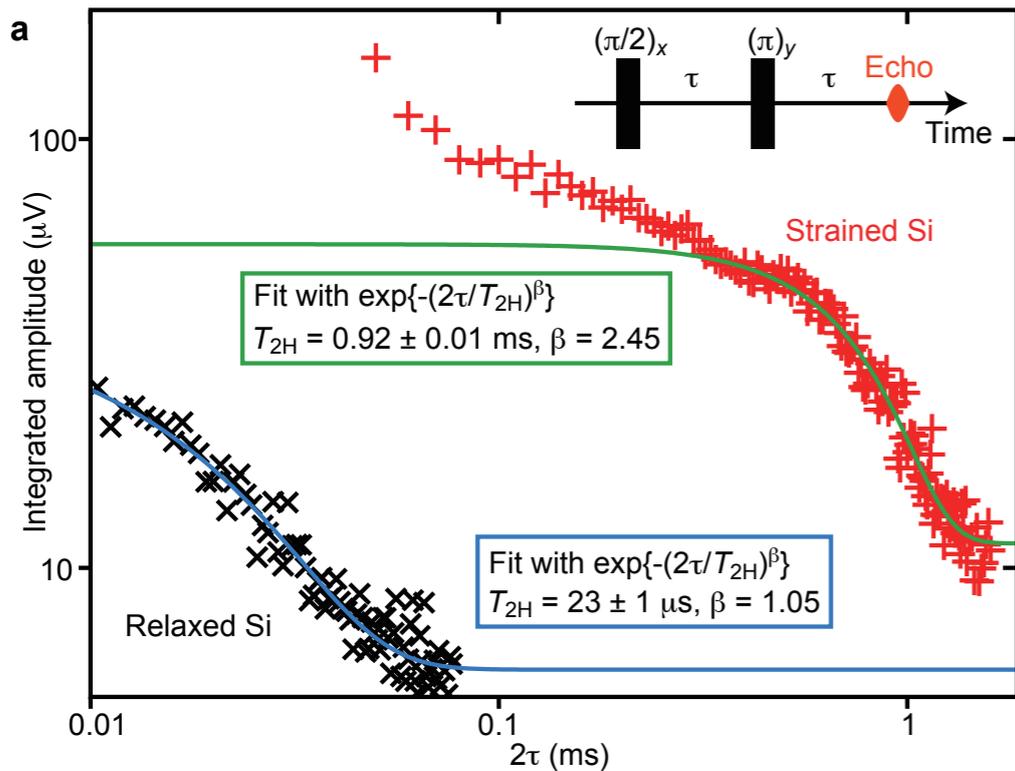
$$hf = g^* \mu_B B$$

$$f = 6.6 \text{ GHz}$$

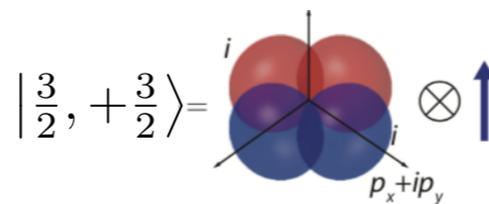
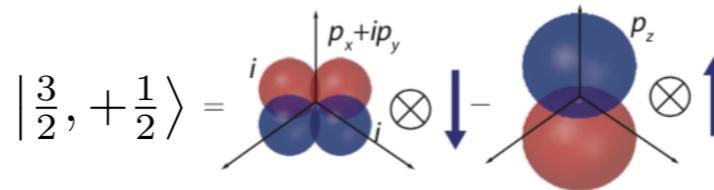
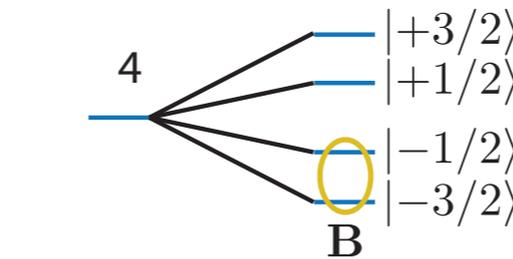




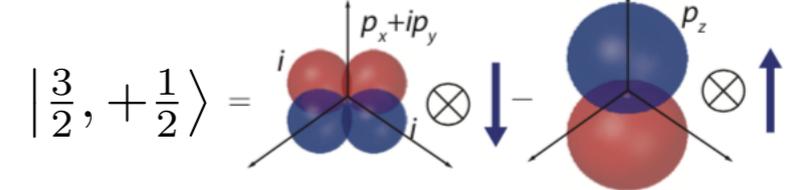
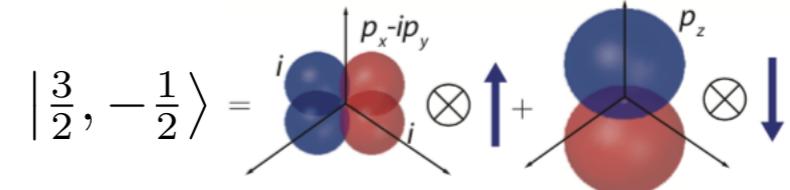
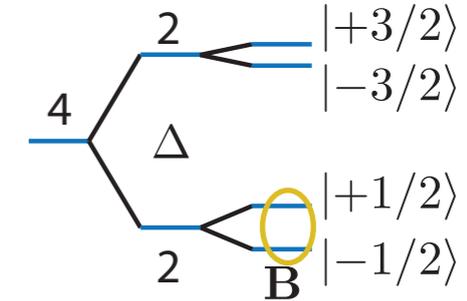
Hole spin coherence



Unstrained ^{28}Si :
 $T_2 = 23 \mu\text{s}, \beta = 1.05$



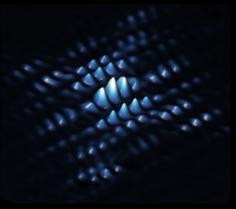
Strained ^{28}Si :
 $T_2 = 0.9 \text{ ms}, \beta = 2.45$



Change in β from ~ 1 to > 2 ?

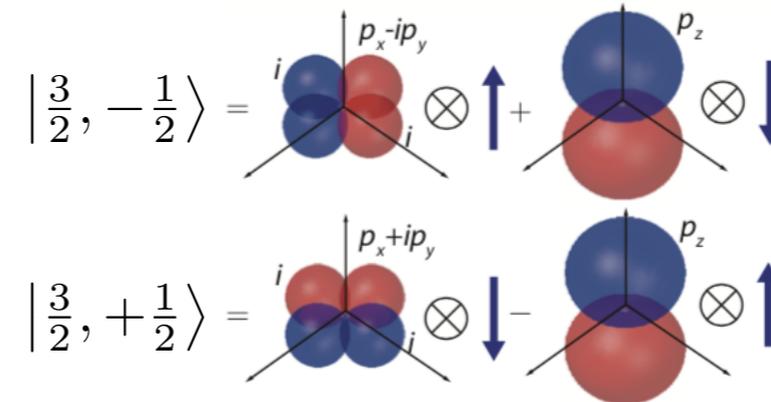
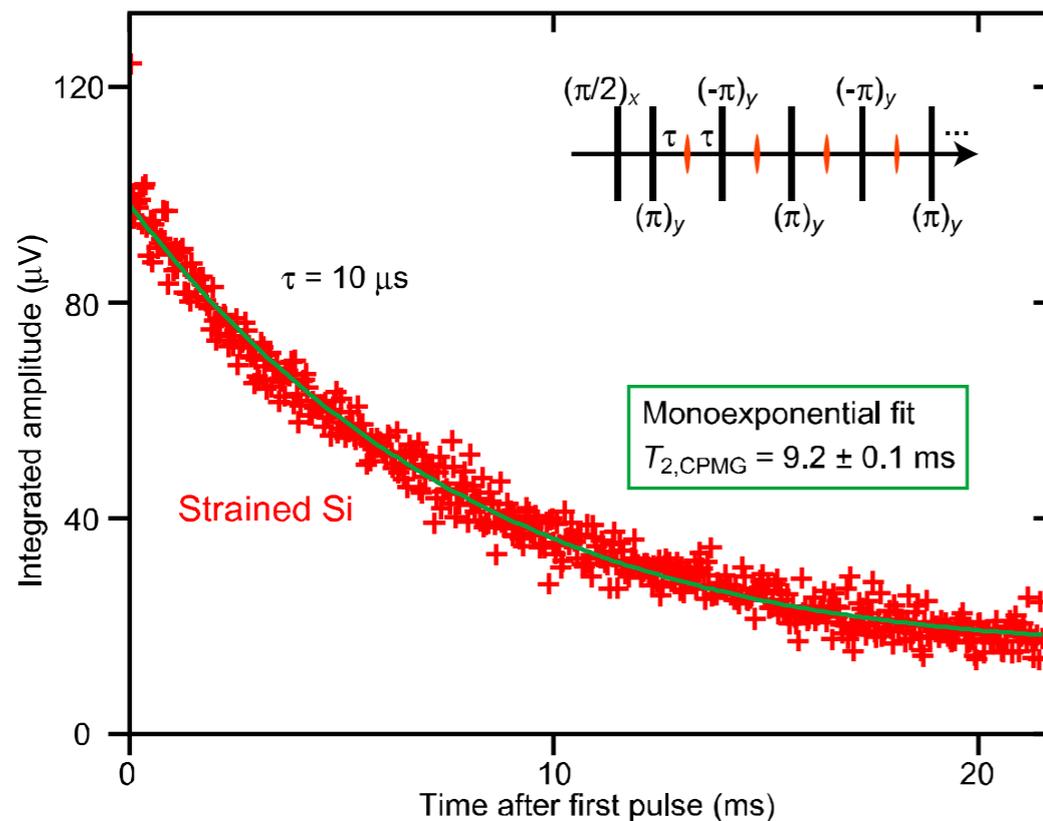
τ_c = correlation time of the fluctuator is changing
 Unstrained : τ_c fast compared to coherence time
 Strained: τ_c slow compared to coherence time

Kobayashi, **Salfi** et al, Nature Materials, 20, 38-42 (2021)

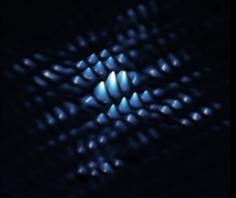


Hole spin coherence

Dynamical decoupling extends coherence time to $T_{2,\text{CPMG}} = 9.2 \text{ ms}$
 Confirms slow fluctuators are limiting coherence in the ensemble



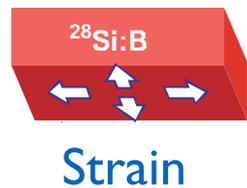
Kobayashi, **Salfi** et al, Nature Materials, 20, 38-42 (2021)



Hole spin coherence

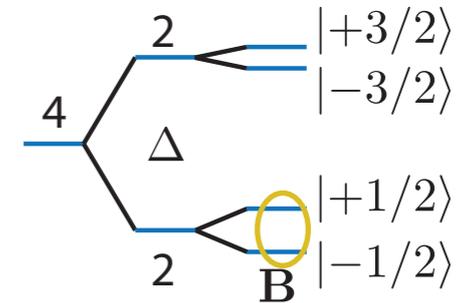
How does the strain improve coherence? $\mathcal{H} = \hbar \left(\omega_0 + \frac{\partial \omega}{\partial E} \delta E \right) \sigma_z + v E_z \sigma_x$

Decoherence is suppressed by the gap



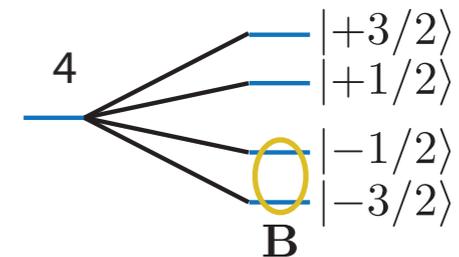
$$\frac{\partial \omega}{\partial E} = \frac{\hbar \omega_0}{2\Delta} p$$

for $\frac{\hbar \omega_0}{\Delta} \ll 1$



c.f. $\frac{\partial \omega}{\partial E} = p$

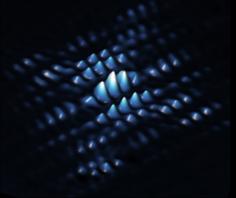
for $\Delta = 0$



Experiment: Reduced longitudinal coupling enhances T_2

- [1] Suppress decoherence from electric fluctuations
- [2] Suppress decoherence from electric dipole-dipole interaction

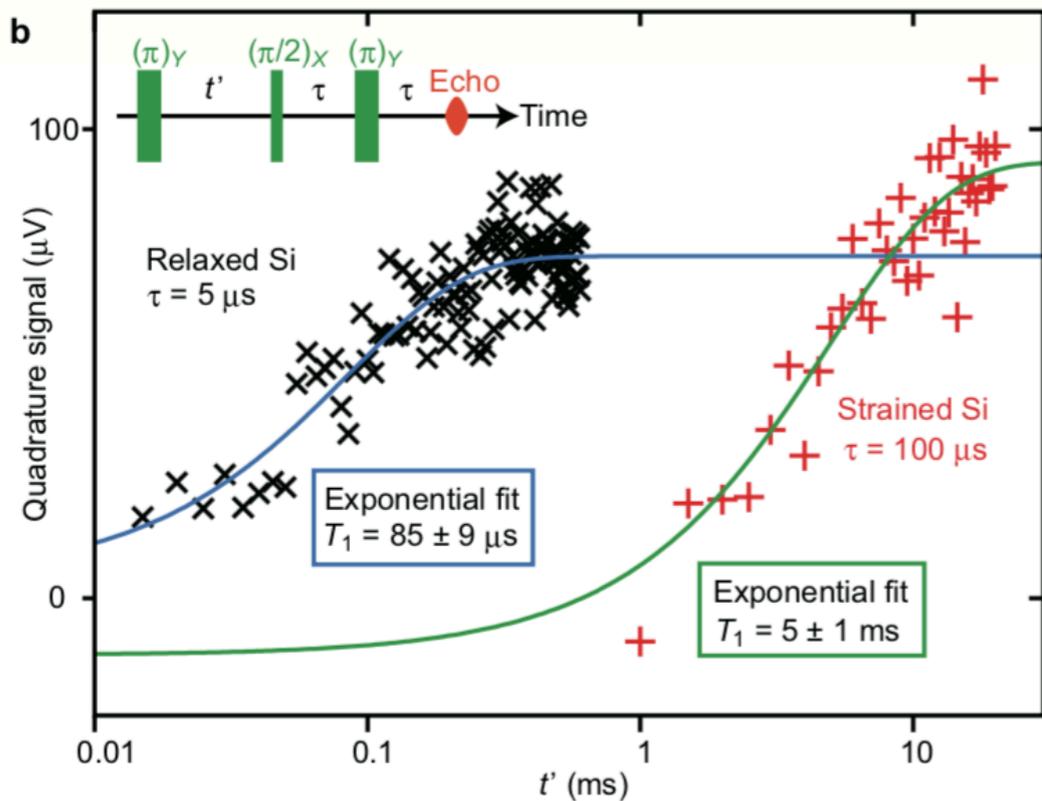
Kobayashi, **Salfi** et al, Nature Materials, 20, 38-42 (2021)



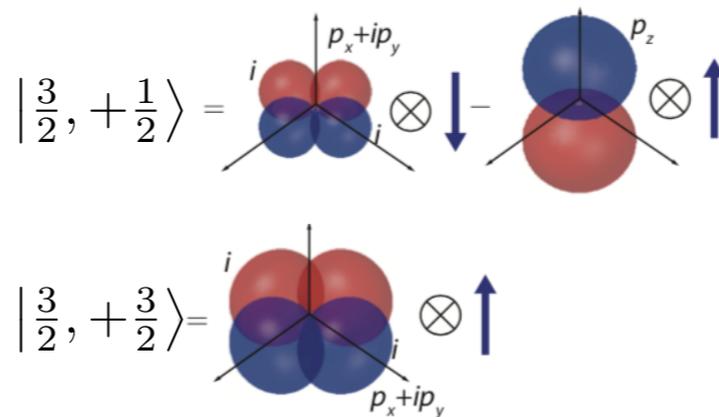
Hole spin coherence

Strained sample also has longer T_1

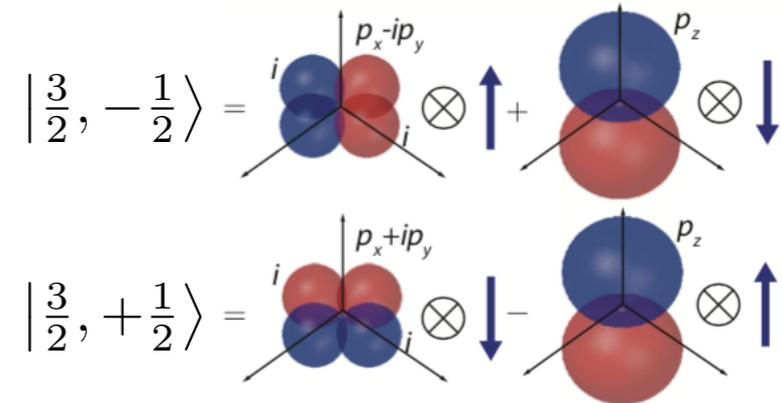
Time-reversal symmetric system inhibits phonon relaxation



Unstrained sample:
 $T_1 = 85 \mu s$



Strained sample:
 $T_1 = 5 \text{ ms}$



9.2 ms $T_{2\text{CPMG}}$ is a close to T_1 -limited spin coherence time

This is not a limitation and T_1 can be improved

Salfi et al, PRL 2016

Abadillo-Uriel et al, APL 2018

Conveniently, T_1 is a good measure of the strain-induced gap

$$\frac{\hbar\omega}{\Delta} \sim \frac{1}{5}$$

Kobayashi, **Salfi** et al, Nature Materials, 20, 38-42 (2021)

Comparison to state-of-the-art

System	T_{2H}	T_{2CPMG}
Si:P e- [1]	4 ms	-
Si:P e- [2]	0.95 ms	~100 ms
Si e- QD [3]	1.2 ms	~28 ms
Si h+ QD [4]	0.25 μ s	-
Si:B h+ no strain	23 μ s	-
Si:B h+ strain	0.9 ms	9 ms

this work

Electron: Donor and QD
~100 ms T_2 of electrons
no electric dipole

- [1] Tyryshkin Nature Mat 2011
- [2] Muhonen Nature Nanotech 2013
- [3] Veldhorst Nature Nanotech 2014
- [4] Maurand Nature Comms 2016

Kobayashi, **Salfi** et al, Nature Materials, 20, 38-42 (2021)



Comparison to state-of-the-art

System	T_{2H}	T_{2CPMG}
Si:P e- [1]	4 ms	-
Si:P e- [2]	0.95 ms	~100 ms
Si e- QD [3]	1.2 ms	~28 ms
Si h+ QD [4]	0.25 μ s	-
Si:B h+ no strain	23 μ s	-
Si:B h+ strain	0.9 ms	9 ms

this work

Hole: QD

~0.25 μ s T_2 of hole QD
with electric dipole

- [1] Tyryshkin Nature Mat 2011
- [2] Muhonen Nature Nanotech 2013
- [3] Veldhorst Nature Nanotech 2014
- [4] Maurand Nature Comms 2016

Kobayashi, **Salfi** et al, Nature Materials, 20, 38-42 (2021)



Comparison to state-of-the-art

System	T_{2H}	T_{2CPMG}
Si:P e- [1]	4 ms	-
Si:P e- [2]	0.95 ms	~100 ms
Si e- QD [3]	1.2 ms	~28 ms
Si h+ QD [4]	0.25 μ s	-
Si:B h+ no strain	23 μ s	-
Si:B h+ strain	0.9 ms	9 ms

this work

Hole: acceptor
 ~ 1 ms T_2
 ~ 10 ms T_{2CPMG}
 with electric dipole

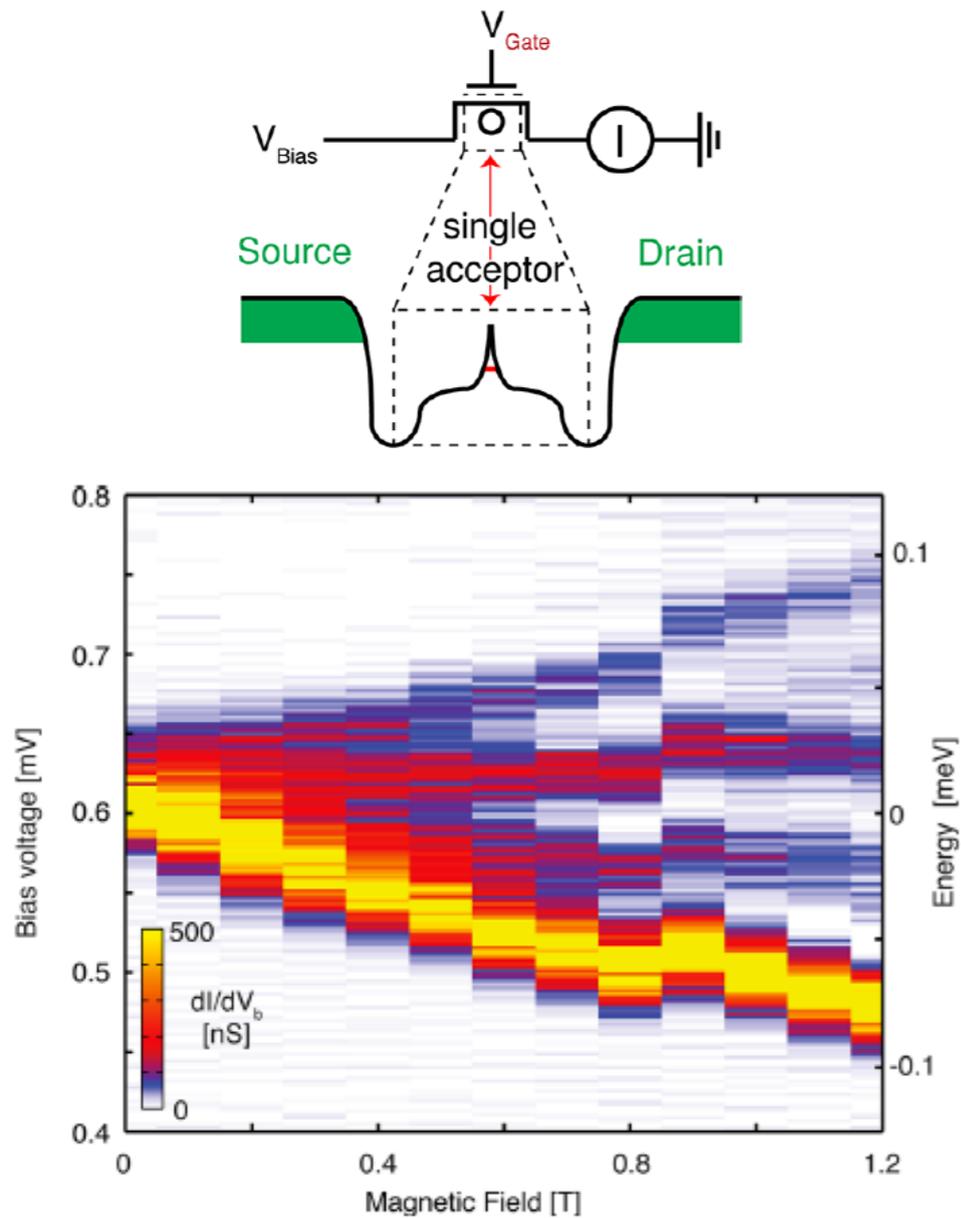
- [1] Tyryshkin Nature Mat 2011
- [2] Muhonen Nature Nanotech 2013
- [3] Veldhorst Nature Nanotech 2014
- [4] Maurand Nature Comms 2016

Intrinsic electric dipoles are compatible with long coherence times
 10^4 to 10^5 times improvement over previous spin-orbit systems

Kobayashi, **Salfi** et al, Nature Materials, 20, 38-42 (2021)

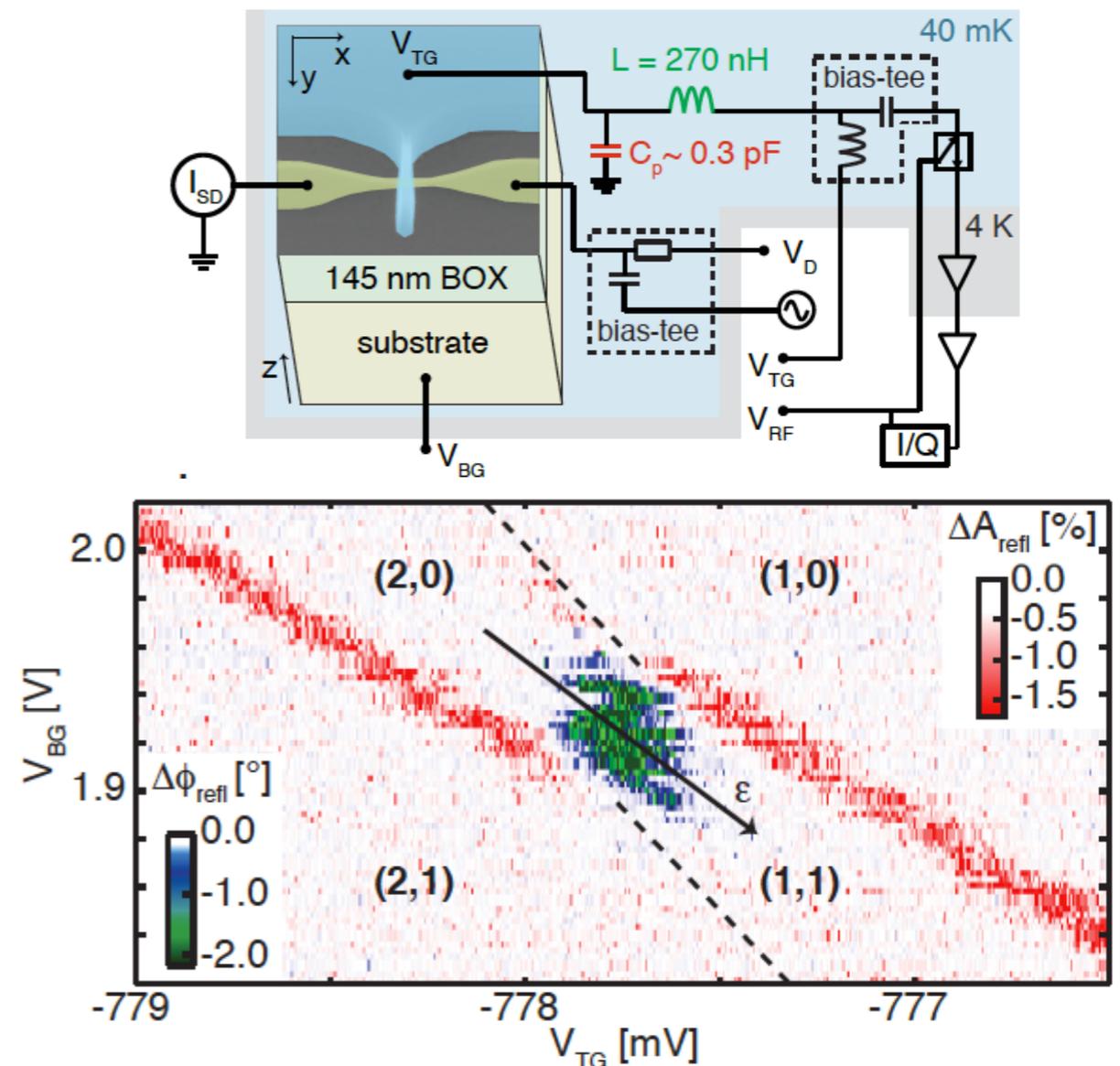
Si:B devices : single and coupled atoms

Single-atom transistor



van der Heijden, **Salfi** et al, Nano Letters 2014

Gate-based spin readout



van der Heijden, Kobayashi, House, **Salfi** et al, Science Advances 2018

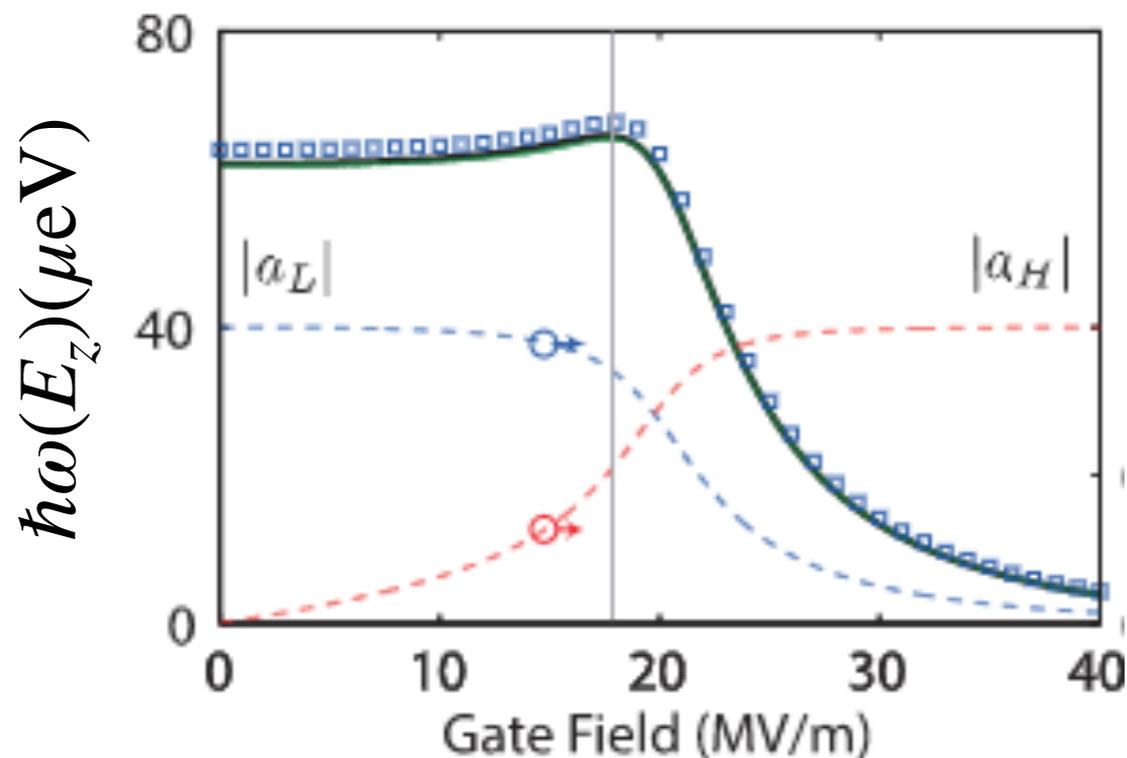
Universality of Group-IV Hole Physics

The theoretical result of long T_1 and long T_2 (robustness to electric fluctuations) with electric control are generic

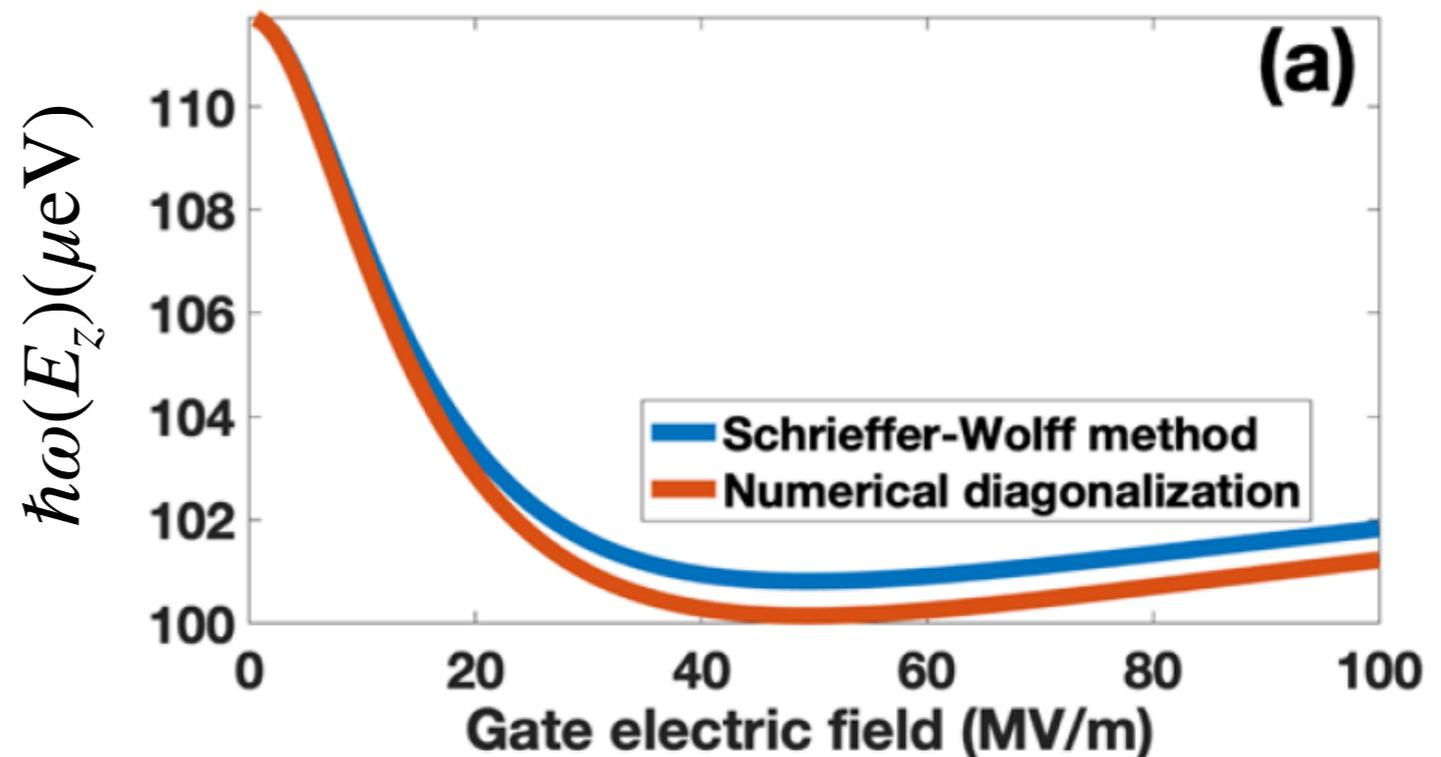
[1] Group IV materials (Rashba, no Dresselhaus SOC): Si or Ge

[2] Confinement potential: impurity (left) or quantum dot (right)

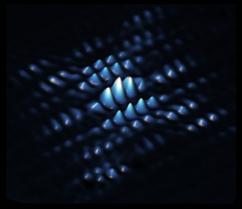
$$\mathcal{H} = \frac{1}{2}\hbar\omega(\mathbf{E})\sigma_z + (\mathbf{v} \cdot \mathbf{E})\sigma_x$$



Salfi et al, Phys. Rev. Lett. 2016



Wang, Marcellina, Hamilton, Cullen, Rogge, **Salfi**, Culcer
Nature PJ Quantum Information, 7, 1-8 (2021))



Thank you!

@UNSW

Takashi Kobayashi

Sven Rogge

Materials

H Riemann

N Abrosimov

P Becker

HJ Pohl

Theory

Dimi Culcer (UNSW)

Bill Coish (hyperfine) (McGill)

B Johnson (Melbourne)

J McCallum (Melbourne)

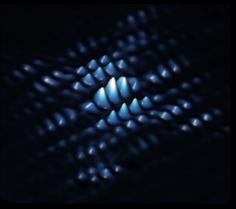


Australian Government
Australian Research Council



Kobayashi, **Salfi** et al, Nature Materials, 2021
Wang et al Nature PJ Quantum Information, 2021
van der Heijden, Kobayashi, House, **Salfi** et al, Science Advances, 2018
Salfi et al, Phys. Rev. Lett. 2016





Thank you!

New Lab @ UBC (QMI)



Current projects on spin qubits

Quantum simulation (Fermionic)

Spin based quantum computation

Gate-based hole-spin quantum dots

Assisted by superconducting technology

More interesting projects coming soon...



NSERC
CRSNG

INNOVATION.CA
CANADA FOUNDATION FOR INNOVATION | FONDATION CANADIENNE POUR L'INNOVATION



THE
UNIVERSITY OF
BRITISH
COLUMBIA



Electrical and
Computer
Engineering